Supporting Information

Improving Device Performance of n-type Organic Field-Effect Transistors via Doping with p-type Organic Semiconductor

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Figure S1 a) Output curve, b) $I_{d1/2}$ vs $V_{GS}$ plot of the pristine and blend OFETs.
Figure S2 Pole figures extracted from the (100) lamellar diffraction for the pristine film and blend films.

Figure S3 Normalized UV-vis absorption spectra of pristine N2200 film, PDVT-8 films and PDVT-8 blended N2200.
**Figure S4** P-type transfer characteristic of the device based on N2200 containing 5% PVDT-8.

**Figure S5** Transfer characteristics of pristine N2200 and its blends with P3HT, DPP-DTT, PCPDTBT and PDVT-8.
Figure S6 Transfer characteristics of pristine P-type polymer PDVT-8 and its blends with 1% PCBM.